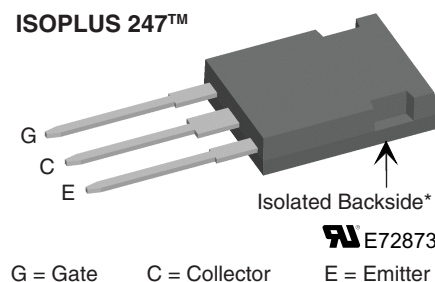
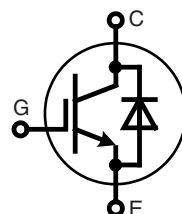


High Voltage IGBT with optional Diode ISOPLUS™ package (Electrically Isolated Back Side)

Short Circuit SOA Capability
Square RBSOA



Symbol	Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C}$ to 150°C	1200	V
V_{CGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GE} = 20\text{ k}\Omega$	1200	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	50	A
I_{C90}	$T_C = 90^\circ\text{C}$	30	A
I_{CM}	$T_C = 90^\circ\text{C}$, $t_p = 1\text{ ms}$	60	A
RBSOA	$V_{GE} = \pm 15\text{ V}$, $T_J = 125^\circ\text{C}$, $R_G = 47\ \Omega$ Clamped inductive load, $L = 30\text{ mH}$	$I_{CM} = 50$ $V_{CEK} < V_{CES}$	A
t_{SC} (SCSOA)	$V_{GE} = \pm 15\text{ V}$, $V_{CE} = V_{CES}$, $T_J = 125^\circ\text{C}$ $R_G = 47\ \Omega$, non repetitive	10	μs
P_c	$T_C = 25^\circ\text{C}$	200 95	W W
T_J		-55 ... +150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
V_{ISOL}	50/60 Hz, RMS $I_{ISOL} \leq 1\text{ mA}$	2500	V~
Weight		6	g

Features

- NPT IGBT technology
 - high switching speed
 - low switching losses
 - square RBSOA, no latch up
 - high short circuit capability
 - positive temperature coefficient for easy paralleling
 - MOS input, voltage controlled
 - fast recovery epitaxial diode
- Epoxy meets UL 94V-0
- Isolated and UL registered E153432

Advantages

- DCB Isolated mounting tab meets TO-247AD package outline
- Package for clip or spring mounting
- Space savings
- High power density

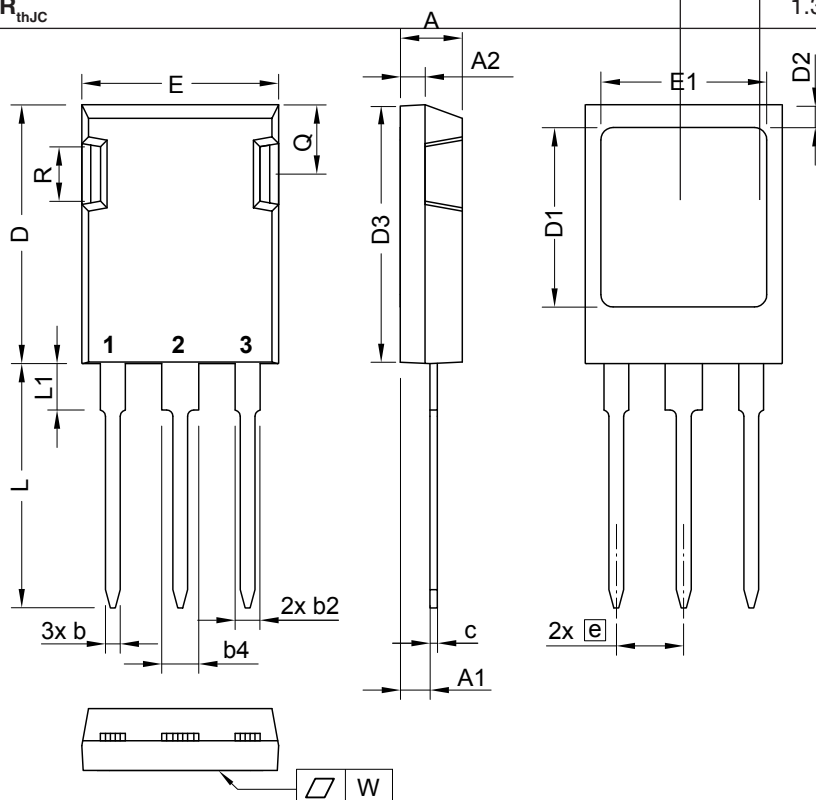
Typical Applications

- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switch-mode and resonant-mode power supplies

Symbol	Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
$V_{(BR)CES}$	$V_{GE} = 0\text{ V}$	1200		V
$V_{GE(th)}$	$I_C = 1\text{ mA}$, $V_{CE} = V_{GE}$	4.5		6.5 V
I_{CES}	$V_{CE} = V_{CES}$, $T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$		2.5	1.5 mA mA
I_{GES}	$V_{CE} = 0\text{ V}$, $V_{GE} = \pm 20\text{ V}$			$\pm 500\text{ nA}$
$V_{CE(sat)}$	$I_C = 30\text{ A}$, $V_{GE} = 15\text{ V}$		2.4	2.9 V

Symbol	Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
C_{ies}	$V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$		1650	pF
C_{oes}			250	pF
C_{res}			110	pF
Q_g	$I_C = 30\text{ A}, V_{GE} = 15\text{ V}, V_{CE} = 0.5 V_{CES}$		120	nC
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = 30\text{ A}, V_{GE} = \pm 15\text{ V},$ $V_{CE} = 600\text{ V}, R_G = 47\ \Omega$		100	ns
t_r			70	ns
$t_{d(off)}$			500	ns
t_f			70	ns
E_{on}			4.6	mJ
E_{off}			3.4	mJ
R_{thJC}	Package with heatsink compound			0.6 K/W
R_{thCH}			0.25	K/W

Reverse Diode (FRED)		Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
Symbol	Conditions	min.	typ.	max.
V_F	$I_F = 30\text{ A}, V_{GE} = 0\text{ V}$	2.5	2.75	V
	$I_F = 30\text{ A}, V_{GE} = 0\text{ V}, T_J = 125^\circ\text{C}$	2.0		V
I_F	$T_C = 25^\circ\text{C}$			50 A
	$T_C = 90^\circ\text{C}$			27 A
I_{RM}	$I_F = 30\text{ A}, -di_F/dt = 400\text{ A}/\mu\text{s}, V_R = 600\text{ V}$	20		A
t_{rr}	$V_{GE} = 0\text{ V}, T_J = 125^\circ\text{C}$	200		ns
t_{rr}	$I_F = 1\text{ A}, -di_F/dt = 100\text{ A}/\mu\text{s}, V_R = 30\text{ V}, V_{GE} = 0\text{ V}$	40		ns
R_{thJC}				1.3 K/W



Dim.	Millimeter		Inches	
	min	max	min	max
A	4.83	5.21	0.190	0.205
A1	2.29	2.54	0.090	0.100
A2	1.91	2.16	0.075	0.085
b	1.14	1.40	0.045	0.055
b1	1.91	2.20	0.075	0.087
b2	2.92	3.24	0.115	0.128
c	0.61	0.83	0.024	0.033
D	20.80	21.34	0.819	0.840
D1	15.75	16.26	0.620	0.640
D2	1.65	2.15	0.065	0.085
D3	20.30	20.70	0.799	0.815
E	15.75	16.13	0.620	0.635
E1	13.21	13.72	0.520	0.540
e	5.45 BSC		0.215 BSC	
L	19.81	20.60	0.780	0.811
L1	3.81	4.38	0.150	0.172
Q	5.59	6.20	0.220	0.244
R	4.25	5.50	0.167	0.217
W	-	0.10	-	0.004

Die konvexe Form des Substrates ist typ. < 0.04 mm über der Kunststoffoberfläche der Bauteilunterseite
The convex bow of substrate is typ. < 0.04 mm over plastic surface level of device bottom side

Die Gehäuseabmessungen entsprechen dem Typ TO-247 AD gemäß JEDEC außer Schraubloch und L_{max} .
This drawing will meet all dimensions requirement of JEDEC outline TO-247 AD except screw hole and except L_{max} .

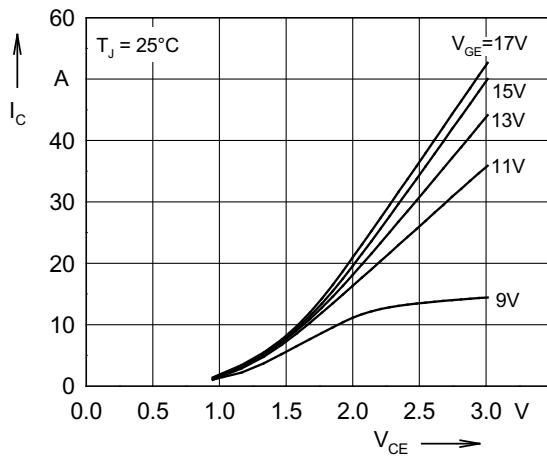


Fig. 1 Typ. output characteristics

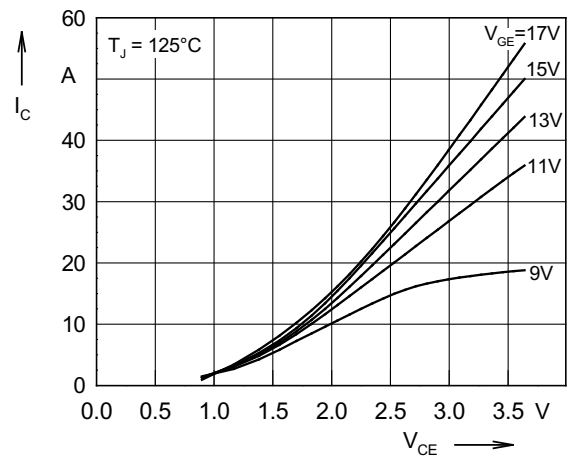


Fig. 2 Typ. output characteristics

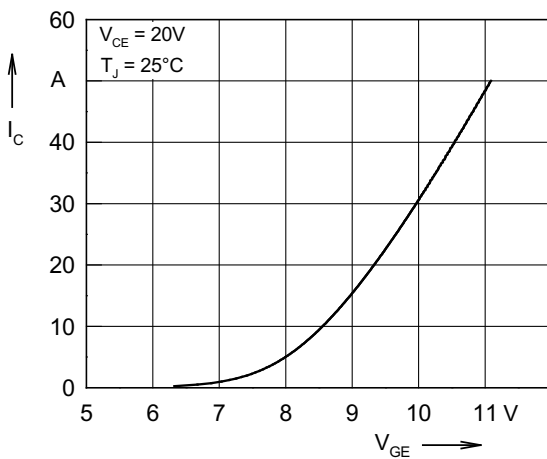


Fig. 3 Typ. transfer characteristics

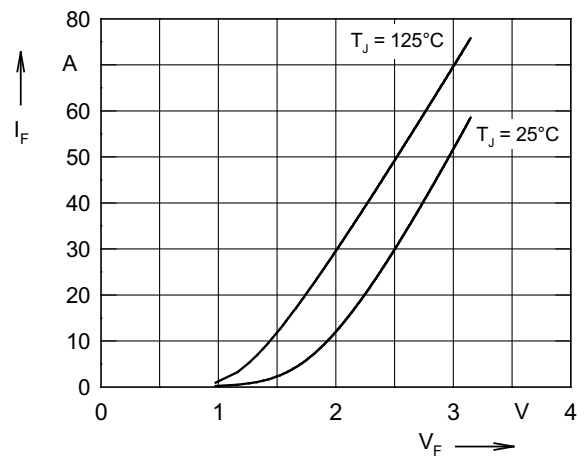


Fig. 4 Typ. forward characteristics of free wheeling diode

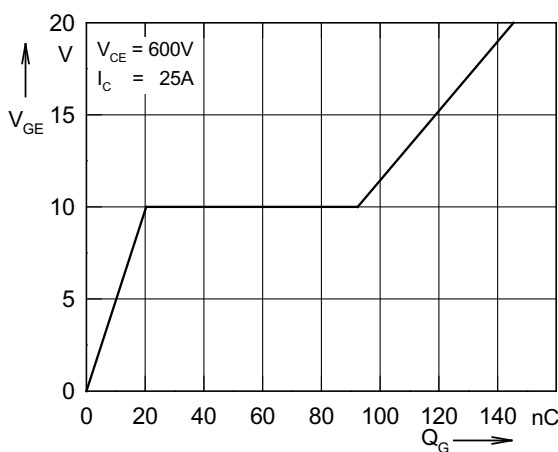


Fig. 5 Typ. turn on gate charge

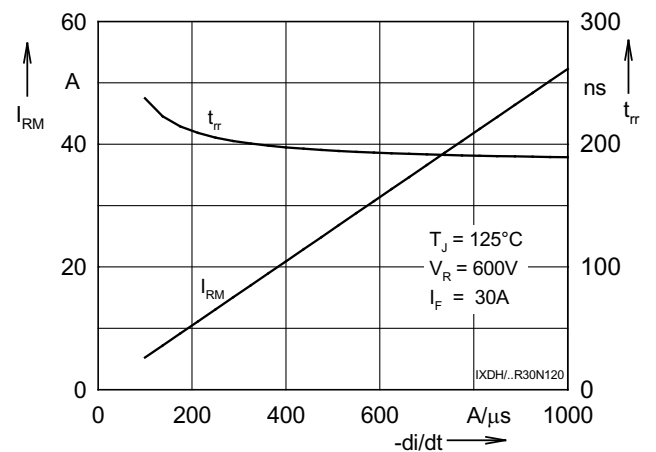


Fig. 6 Typ. turn off characteristics of free wheeling diode

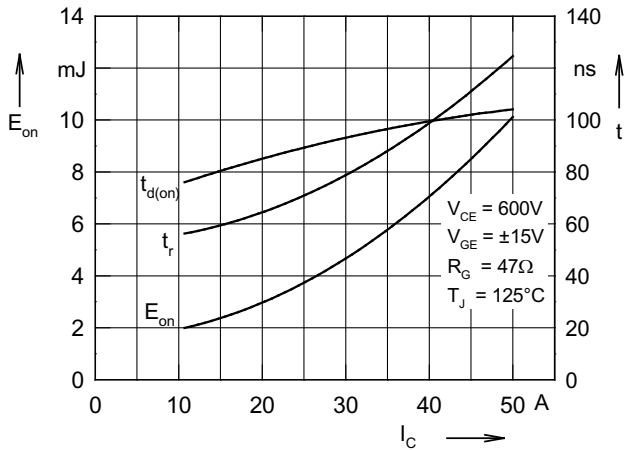


Fig. 7 Typ. turn on energy and switching times versus collector current

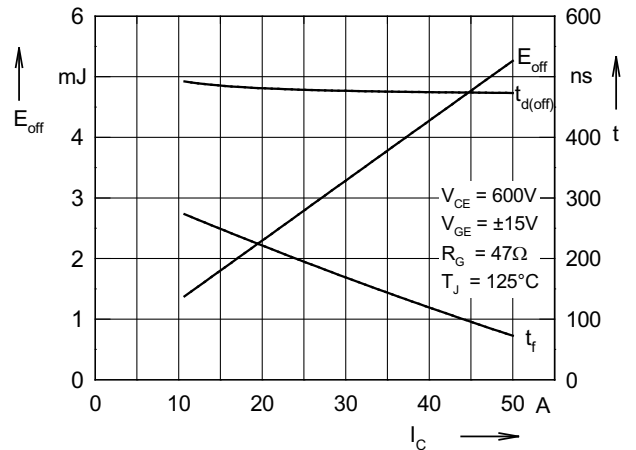


Fig. 8 Typ. turn off energy and switching times versus collector current

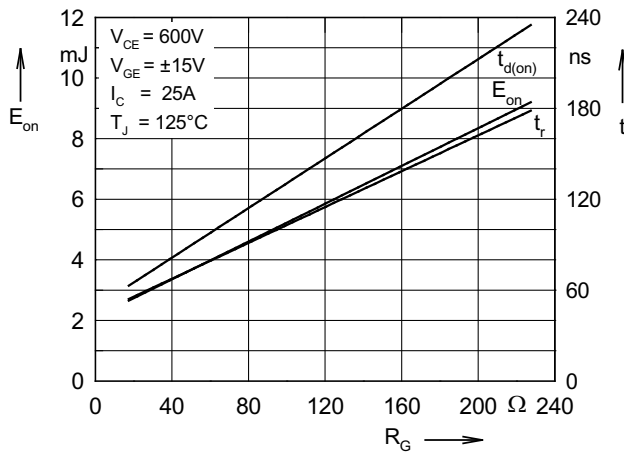


Fig. 9 Typ. turn on energy and switching times versus gate resistor

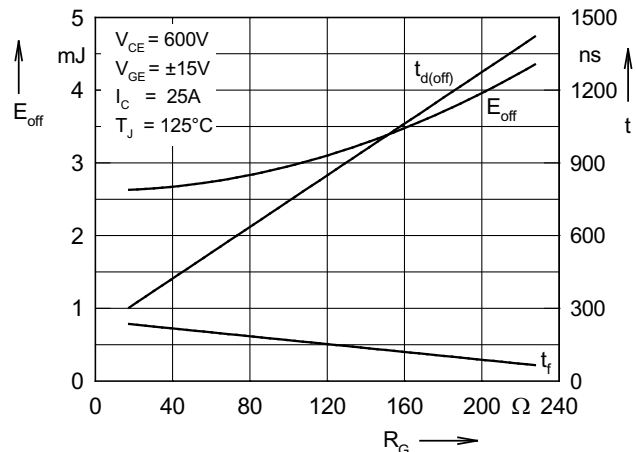


Fig. 10 Typ. turn off energy and switching times versus gate resistor

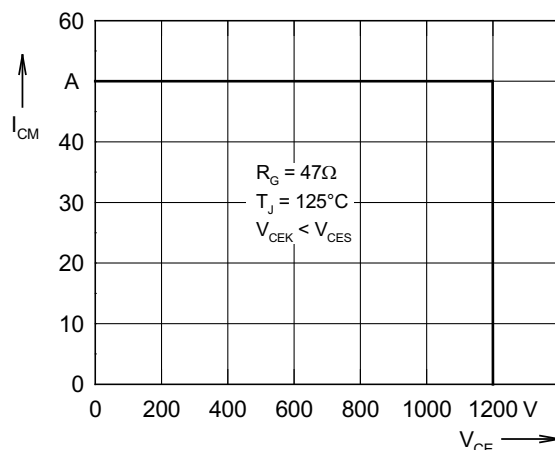


Fig. 11 Reverse biased safe operating area RBSOA

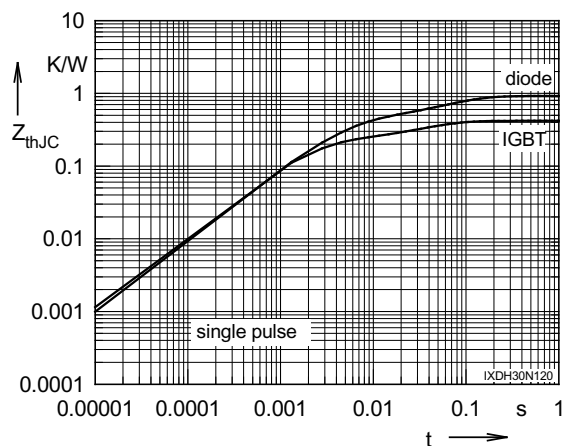


Fig. 12 Typ. transient thermal impedance

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